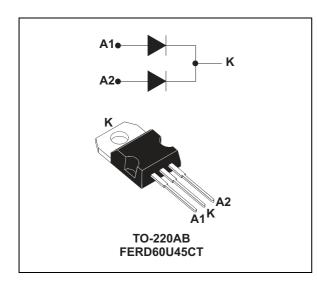


FERD60U45C

Field effect rectifier

Datasheet - production data



Description

This dual rectifier is based on a proprietary technology that achieves the best in class $V_{\text{F}}/I_{\text{R}}$ for a given silicon surface.

Packaged in TO-220AB, this device is intended to be used in switch mode power supplies, or automotive applications

Table 1. Device summary

I _{F(AV)}	2 x 30 A
V _{RRM}	45 V
V _F (typ)	0.345 V

Features

- ST advanced rectifier process
- Stable leakage current over reverse voltage
- Low forward voltage drop
- High frequency operation

This is information on a product in full production.

1 Characteristics

Table 2. Absolute ratings (limiting values, per diode at 25° C, unless otherwise stated)

Symbol	Para	Value	Unit		
V _{RRM}	Repetitive peak reverse voltage			45	V
I _{F(RMS)}	Forward rms current	60	А		
I _{F(AV)}	$ \begin{array}{ll} \mbox{Average forward current, $\delta = 0.5$} & \begin{array}{c} T_c = 145^{\circ} \ C & \\ T_c = 135^{\circ} \ C & \\ \end{array} \begin{array}{l} \mbox{Per diode} \\ \mbox{Per device} \end{array} \end{array} $		30 60	А	
I _{FSM}	Surge non repetitive forward current t _p = 10 ms sinusoidal			300	А
T _{stg}	Storage temperature range			-65 to + 175	°C
Тj	Maximum operating junction temperature ⁽¹⁾ 175			°C	

1. $\frac{dPtot}{dT_i} < \frac{1}{Rth(i-a)}$ condition to avoid thermal runaway for a diode on its own heatsink

Table 3. Thermal resistances

Symbol	Parameter	Value	Unit	
R _{th (j-c)}	Junction to case	Per diode Total	1.4 0.9	°C/W
R _{th(c)}	Coupling		0.4	°C/W

When the diodes 1 and 2 are used simultaneously:

 $\Delta T_{j}(diode \ 1) = P(diode1) \ x \ R_{th(j-c)}(Per \ diode) + P(diode2) \ x \ R_{th(c)}.$

Symbol	Parameter	Test Con	ditions	Min.	Тур.	Max.	Unit
I _R ⁽¹⁾	Povorso lookago ourront	T _j = 25° C	V _ V			1500	μA
I _R ⁽¹⁾ Reverse leakage current	neverse leakage current	T _j = 125° C	V _R = V _{RRM}		50	100	mA
	$T_{j} = 25^{\circ} C$ $T_{j} = 125^{\circ} C$ $I_{F} = 15 A$	T _j = 25° C			0.38	0.41	
V _F ⁽²⁾		1 _F = 15 A		0.345	0.375	v	
V F` ´	Forward voltage drop	T _j = 25° C	I _F = 30 A		0.46	0.50	
		T _j = 125° C	1F = 30 A		0.47	0.51	

1. Pulse test: $t_p = 5 \text{ ms}, \delta < 2\%$

2. Pulse test: t_p = 380 µs, δ < 2%

To evaluate the conduction losses use the following equation:

 $P = 0.32 \times I_{F(AV)} + 0.0063 I_{F}^{2}(RMS)$



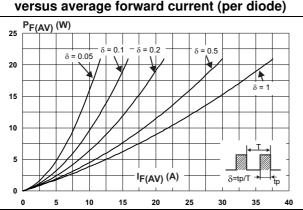
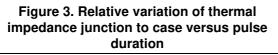


Figure 1. Average forward power dissipation versus average forward current (per diode)



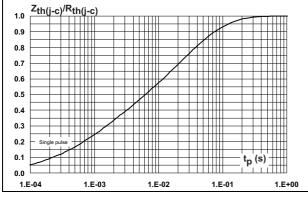
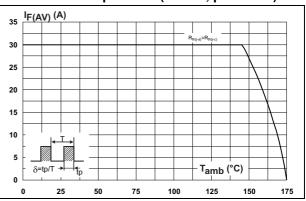
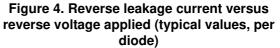




Figure 2. Average forward current versus ambient temperature (δ = 0.5, per diode)





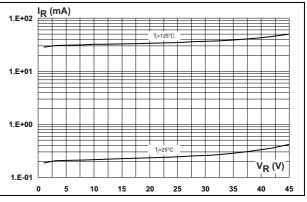
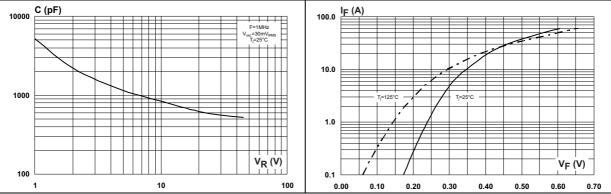


Figure 6. Forward voltage drop versus forward current (typical values, per diode)

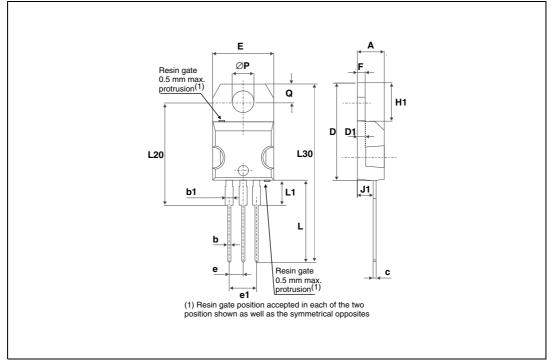




2 Package Information

- Epoxy meets UL94,V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.4 to 0.6 N·m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK[®] is an ST trademark.



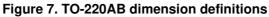




Table 5. TO-220AB dimension values					
	Dimensions				
Ref.	Millim	eters	Inc	hes	
	Min.	Max.	Min.	Max.	
А	4.40	4.60	0.17	0.18	
b	0.61	0.88	0.024	0.035	
b1	1.14	1.70	0.045	0.067	
С	0.48	0.70	0.019	0.027	
D	15.25	15.75	0.60	0.62	
D1	1.27 typ.		0.05	typ.	
Е	10	10.40	0.39	0.41	
е	2.40	2.70	0.094	0.106	
e1	4.95	5.15	0.19	0.20	
F	1.23	1.32	0.048	0.052	
H1	6.20	6.60	0.24	0.26	
J1	2.40	2.72	0.094	0.107	
L	13	14	0.51	0.55	
L1	3.50	3.93	0.137	0.154	
L20	16.40 typ.		0.64	typ.	
L30	28.90	typ.	1.13	typ.	
ØP	3.75	3.85	0.147	0.151	
Q	2.65	2.95	0.104	0.116	

Table 5. TO-220AB dimension values



3 Ordering Information

Table (6. (Ordering	information
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Order code	Marking	Package	Weight	Base qty	Delivery mode
FERD60U45CT	FERD60U45CT	TO-220AB	2.2 g	50	Tube

4 Revision history

Table 7. Document revision histor	Table 7.	. Documen	t revision	history
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Date	Revision	Description of Changes
13-Nov-2013	1	Previous version



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